

# AOZ5007AQI

High-Current, High-Performance
DrMOS Power Module

## **General Description**

AOZ5007AQI is a high efficiency synchronous buck power stage module consisting of two asymmetrical MOSFETs and an integrated driver. The MOSFETs are individually optimized for operation in the synchronous buck configuration. The High-Side MOSFET is optimized to achieve low capacitance and gate charge for fast switching with low duty cycle operation. The Low-Side MOSFET has ultra-low ON resistance to minimize conduction loss.

AOZ5007AQI uses a PWM input for accurate control of the power MOSFETs switching activities, is compatible with 5V (CMOS) logic and supports Tri-State PWM.

A number of features are provided making the AOZ5007AQI a highly versatile power module. The bootstrap diode is integrated in the driver. The Low-Side MOSFET can be driven into diode emulation mode to provide asynchronous operation and improve light-load performance. The pin-out is also optimized for low parasitics, keeping their effects to a minimum.

#### **Features**

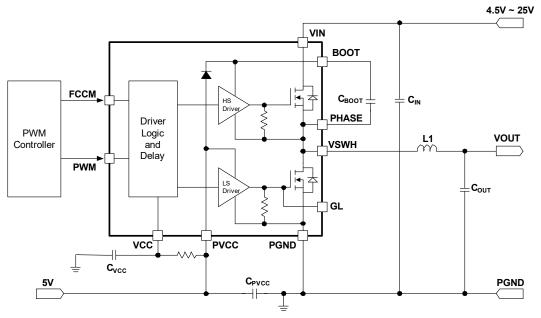
- 4.5V to 25V power supply range
- 4.5V to 5.5V driver supply range
- 30A continuous output current
  - Up to 65A with 20ms instantaneous current @ 14V VIN
  - Up to 60A with 20ms instantaneous current @ 22V VIN
  - Up to 80A with 10us on pulse
- Up to 2MHz switching operation
- 5V PWM / Tri-State input compatible
- Under-Voltage LockOut protection
- FCCM control for Diode Emulation / CCM operation
- Low Profile 3.5mm x 4.5mm QFN-22L package

#### **Applications**

- Memory and graphic cards
- VRMs for motherboards
- Point of load DC/DC converters
- Video gaming console



# **Typical Application Circuit**





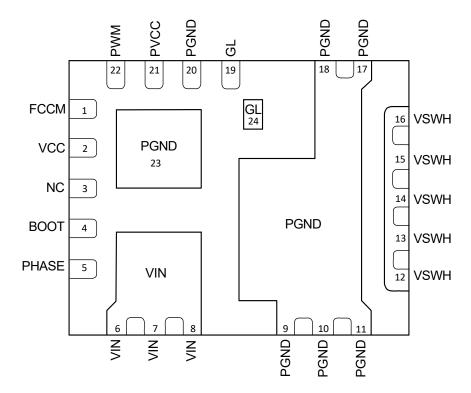
# **Ordering Information**

Part Number Junction Temperatu		Junction Temperature Range	Package	Environmental
	AOZ5007AQI -40°C to +125°C		QFN3.5x4.5-22L	RoHS



AOS Green Products use reduced levels of Halogens, and are also RoHS compliant. Please visit www.aosmd.com/media/AOSGreenPolicy.pdf for additional information.

# **Pin Configuration**



QFN3.5x4.5-22L (Top Transparent View)

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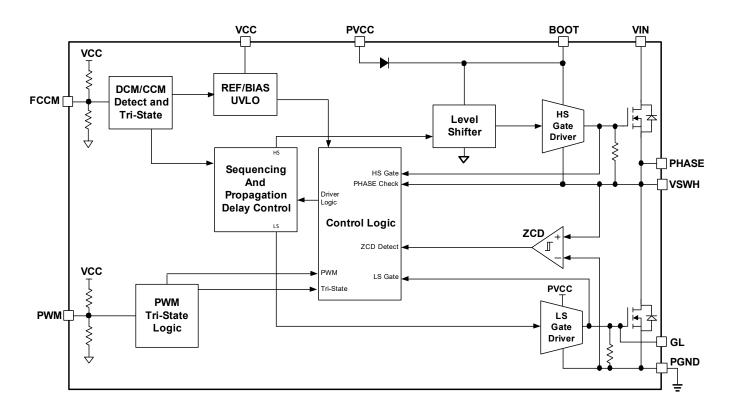


# **Pin Description**

Pin Number Pin Name		Pin Function			
1 FCCM Discontinuous mode is allowed and diode emulation		Continuous conduction mode of operation is allowed when FCCM = High.  Discontinuous mode is allowed and diode emulation mode is active when FCCM = Low.  High impedance on the input of FCCM will shut down both High-Side and Low-Side MOSFETs.			
2 VCC 5V Bias for Internal Logic Blocks. Ensure to position a 1μF MLCC PGND (Pin 20).		5V Bias for Internal Logic Blocks. Ensure to position a 1μF MLCC directly between VCC and PGND (Pin 20).			
3	NC	No connect. Internally connected to PGND paddle. It can be left floating (no connect) or tied to PGND.			
4 BOOT High-Side MOSFET Gate Driver supply rail. Connect a 100nF ce BOOT and the PHASE (Pin 5).		High-Side MOSFET Gate Driver supply rail. Connect a 100nF ceramic capacitor between BOOT and the PHASE (Pin 5).			
5	PHASE	This pin is dedicated for bootstrap capacitor AC return path connection from BOOT (Pin 4).			
9, 10, 11, 17, 18 PGND Power 12, 13, 14, 15, 16 VSWH MOSFE		Power stage High Voltage Input (Drain connection of High-Side MOSFET).			
		Power Ground pin for power stage (Source connection of Low-Side MOSFET).			
		Switching node connected to the Source of High-Side MOSFET and the Drain of Low-Side MOSFET. These pins are used for Zero Cross Detection and Anti-Overlap Control as well as main inductor terminal.			
19, 24	GL	Low-Side MOSFET Gate connection. This is for test purposes only. AOS recommends to omit GL (Pin 24) from land pattern. Pin 19 and Pin 24 are electrically connected inside the package.			
20, 23 PGND directly betw 21 PVCC 5V Power R directly betw		Power Ground pin for High-Side and Low-Side MOSFET Gate Drivers. Ensure to connect 1µF directly between PGND and PVCC (Pin 21).			
		5V Power Rail for High-Side and Low-Side MOSFET Drivers. Ensure to position a 1μF MLCC directly between PVCC and PGND (Pin 20).			
		PWM input signal from the controller IC. This input is compatible with 5V and Tri-State logic levels.			



# **Functional Block Diagram**





# **Absolute Maximum Ratings**

Exceeding the Absolute Maximum ratings may damage the device.

Parameter	Rating			
Low Voltage Supply (VCC, PVCC)	-0.3V to 7V			
High Voltage Supply (VIN)	-0.3V to 30V			
Control Inputs (PWM, FCCM)	-0.3V to (VCC+0.3V)			
Bootstrap Voltage DC (BOOT-PGND)	-0.3V to 33V			
Bootstrap Voltage Transient <sup>(1)</sup> (BOOT-PGND)	-8V to 40V			
Bootstrap Voltage DC (BOOT-PHASE/VSWH)	-0.3V to 7V			
BOOT Voltage Transient <sup>(1)</sup> (BOOT-PHASE/VSWH)	-0.3V to 9V			
Switch Node Voltage DC (PHASE/VSWH)	-0.3V to 30V			
Switch Node Voltage Transient <sup>(1)</sup> (PHASE/VSWH)	-8V to 38V			
Low-Side Gate Voltage DC (GL)	(PGND-0.3V) to (PVCC+0.3V)			
Low-Side Gate Voltage Transient <sup>(2)</sup> (GL)	(PGND-2.5V) to (PVCC+0.3V)			
VSWH Current DC	30A			
VSWH Current 20ms Pulse @ 14V VIN	65A			
VSWH Current 20ms Pulse @ 22V VIN	60A			
VSWH Current 10us Pulse	80A			
Storage Temperature (T <sub>S</sub> )	-65°C to +150°C			
Max Junction Temperature (T <sub>J</sub> )	150°C			
ESD Rating <sup>(3)</sup>	2kV			

#### Notes:

- 1. Peak voltages can be applied for 10ns per switching cycle.
- 2. Peak voltages can be applied for 20ns per switching cycle.
- 3. Devices are inherently ESD sensitive, handling precautions are required. Human body model rating: 1.5 $\Omega$  in series with 100pF.

# **Recommended Operating Conditions**

The device is not guaranteed to operate beyond the Maximum Recommended Operating Conditions.

Parameter	Rating
High Voltage Supply (VIN)	4.5V to 25V
Low Voltage / MOSFET Driver Supply (VCC, PVCC)	4.5V to 5.5V
Control Inputs (PWM, FCCM)	0V to VCC
Operating Frequency	200kHz to 2MHz



# Electrical Characteristics<sup>(4)</sup>

TJ = 0°C to 150°C, VIN = 12V, VOUT = 1V, PVCC = VCC = 5V, unless otherwise specified. Min/Max values are guaranteed by test, design or statistical correlation.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
GENERAL			l .	II.	<u> </u>	
V <sub>IN</sub>	Power Stage Power Supply		4.5		25	V
V <sub>CC</sub>	Low Voltage Bias Supply	PVCC = VCC	4.5		5.5	V
$R_{\theta JC}^{(4)}$	The amount Desciotes and	PCB Temp = 100°C		2.5		°C / W
R <sub>0JA</sub> (4)	- Thermal Resistance			18.5		°C / W
INPUT SUP	PLY AND UVLO		1	1		
V <sub>CC_UVLO</sub>	Under veltage LeekOut	VCC Rising		3.4	3.9	V
V <sub>CC_HYST</sub>	- Under-voltage LockOut	VCC Hysteresis		500		mV
<del>-</del>		FCCM = Floating, PWM = Floating		3	5	μA
$I_{VCC}$	Control Circuit Bias Current	FCCM = 5V, PWM = Floating		80		μA
		FCCM = 0V, PWM = Floating		120		μA
PWM INPU	r ·		1	· ·	•	
V <sub>PWM_H</sub>	Logic High Input Voltage		4.2			V
V <sub>PWM_L</sub>	Logic Low Input Voltage				0.72	V
I <sub>PWM_SRC</sub>	DIAMA Die leeut Coment	PWM = 0V		-250		μA
I <sub>PWM_SNK</sub>	- PWM Pin Input Current	PWM = 5V		250		μA
V <sub>TRI</sub>	PWM Tri-State Window		1.6		3.4	V
FCCM INPU	JT		1	1		
V <sub>FCCM_H</sub>	Logic High Input Voltage		3.9			V
V <sub>FCCM_L</sub>	Logic Low Input Voltage				1.1	V
	FOOM Die leest Owen et	FCCM = 0V		50		μA
I <sub>FCCM</sub>	FCCM Pin Input Current	FCCM = 5V		-50		μA
V <sub>TRI</sub>	FCCM Tri-State Window		2.1		2.9	V
t <sub>PS4_EXIT</sub>	PS4 Exit Latency			2.5	5	μs
	ER TIMINGS			1	1	
t <sub>PDLU</sub>	PWM to HS Gate	PWM: $H \rightarrow L$ , VSWH: $H \rightarrow L$		18		ns
t <sub>PDLL</sub>	PWM to LS Gate	PWM: $L \rightarrow H$ , GL: $H \rightarrow L$		25		ns
t <sub>PDHU</sub>	LS to HS Gate Deadtime	GL: $H \rightarrow L$ , VSWH: $L \rightarrow H$		20		ns
t <sub>PDHL</sub>	HS to LS Gate Deadtime	VSWH: $H \rightarrow 1V$ , GL: $L \rightarrow H$		20		ns
t <sub>TSSHD</sub>	Tri-State Shutdown Delay	PWM: $L \rightarrow V_{TRI}$ , GL: $H \rightarrow L$ and PWM: $H \rightarrow V_{TRI}$ , VSWH: $H \rightarrow L$		150		ns
t <sub>TSEXIT</sub> Tri-State Propagation Delay		$\begin{array}{c} \text{PWM: V}_{\text{TRI}} \rightarrow \text{H, VSWH: L} \rightarrow \text{H} \\ \text{PWM: V}_{\text{TRI}} \rightarrow \text{L, GL: L} \rightarrow \text{H} \end{array}$		35		ns
t <sub>LGMIN</sub>	LS Minimum On Time	FCCM = 0V		550		ns

#### Notes:

- 4. All voltages are specified with respect to the corresponding AGND pin.
- 5. Characterization value. Not tested in production.

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# **Timing Diagrams**

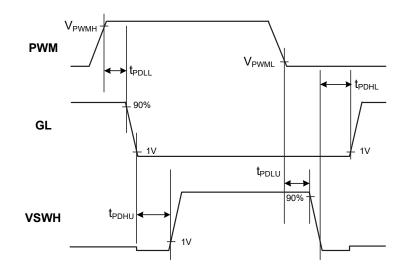


Figure 1. PWM Logic Input Timing Diagram

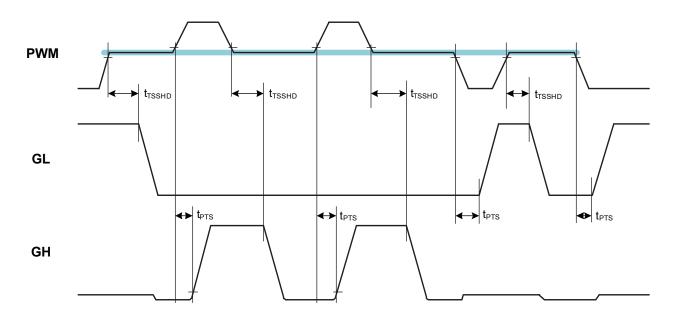


Figure 2. PWM Tri-State Hold Off and Exit Timing Diagram

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## **Typical Performance Characteristics**

 $T_A = 25$ °C, VIN = 12V, VOUT = 1V, PVCC = VCC = 5V, unless otherwise specified.

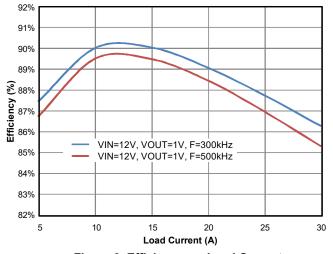


Figure 3. Efficiency vs. Load Current

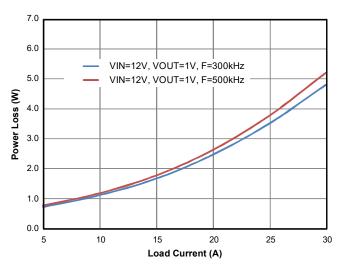


Figure 4. Power Loss vs. Load Current

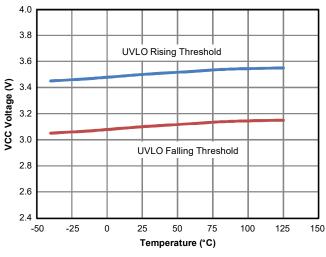


Figure 5. UVLO (VCC) Threshold vs. Temperature

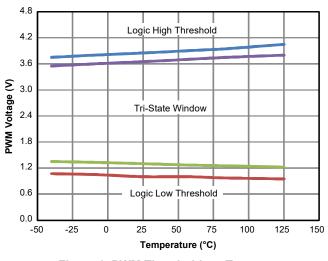


Figure 6. PWM Threshold vs. Temperature

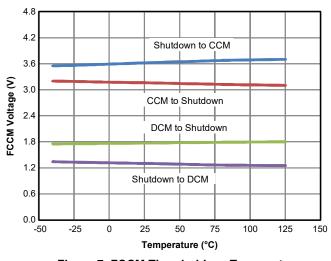


Figure 7. FCCM Threshold vs. Temperature

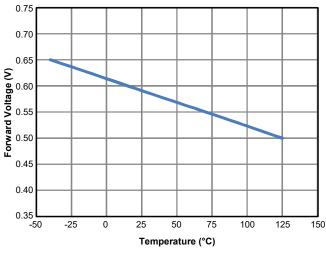


Figure 8. Boot Diode Forward Voltage vs. Temperature

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# **Typical Performance Characteristics** (Continued)

 $T_A = 25$ °C, VIN = 12V, VOUT = 1V, PVCC = VCC = 5V, unless otherwise specified.

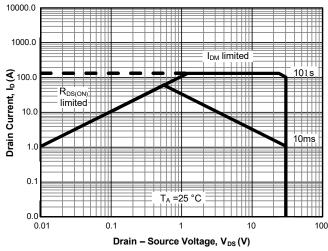


Figure 9. High-Side MOSFET SOA

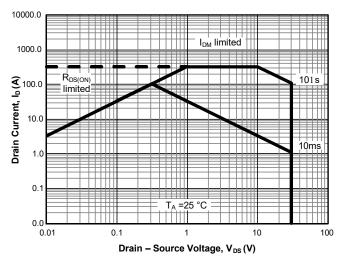


Figure 10. Low-Side MOSFET SOA



#### **Application Information**

AOZ5007AQI is a fully integrated power module designed to work over an input voltage range of 4.5V to 25V with a separate 5V supply for gate drive and internal control circuitry. The MOSFETs are individually optimized for efficient operation on both High-Side and Low-Side for a low duty cycle synchronous buck converter. High current MOSFET Gate Drivers are integrated in the package to minimize parasitic loop inductance for optimum switching efficiency.

#### **Powering the Module and the Gate Drives**

An external supply PVCC = 5V is required for driving the MOSFETs. The MOSFETs are designed with optimally customized gate thresholds voltages to achieve the most advantageous compromise between fast switching speed and minimal power loss. The integrated gate driver is capable of supplying large peak current into the Low-Side MOSFET to achieve fast switching. A ceramic bypass capacitor of  $1\mu F$  or higher is recommended from PVCC (Pin 21) to PGND (Pin 20). The control logic supply VCC (Pin 2) can be derived from the gate drive supply PVCC (Pin 21) through an RC filter to bypass the switching noise (See Typical Application Circuit).

The boost supply for driving the High-Side MOSFET is generated by connecting a small capacitor (100nF) between the BOOT (Pin 4) and the switching node PHASE (Pin 5). It is recommended that this capacitor  $C_{BOOT}$  should be connected to the device across Pin 4 and Pin 5 as close as possible. A bootstrap diode is integrated into the device to reduce external component count. An optional resistor  $R_{BOOT}$  in series with  $C_{BOOT}$  between  $1\Omega$  to  $5\Omega$  can be used to slow down the turn on speed of the High-Side MOSFET to achieve both short switching time and low VSWH switching node spikes at the same time.

#### **Under-voltage LockOut**

AOZ5007AQI starts up to normal operation when VCC rises above the Under-Voltage LockOut (UVLO) threshold voltage. The UVLO release is set at 3.5V typically. Since the PWM control signal is provided from an external controller or a digital processor, extra caution must be taken during start up. AOZ5007AQI must be powered up before PWM input is applied.

Normal system operation begins with a soft start sequence by the controller to minimize in-rush current during start up. Powering the module with a full duty cycle PWM signal may lead to many undesirable consequences due to excessive power. AOZ5007AQI provides some protections such as UVLO and thermal monitor. For system level protection, the PWM controller should monitor the current output and protect the load under all possible operating and transient conditions.

#### **Input Voltage VIN**

AOZ5007AQI is rated to operate over a wide input range from 4.5V to 25V. For high current synchronous buck converter applications, large pulse current at high frequency and high current slew rates (di/dt) will be drawn by the module during normal operation. It is strongly recommended to place a bypass capacitor very close to the package leads at the input supply (VIN). Both X7R or X5R quality surface mount ceramic capacitors are suitable.

The High-Side MOSFET is optimized for fast switching by using a low gate charge  $(\mathsf{Q}_G)$  device. When the module is operated at high duty cycle ratio, conduction loss from the High-Side MOSFET will be higher. The total power loss for the module is still relatively low but the High-Side MOSFET higher conduction loss may have higher temperature. The two MOSFETs have their own exposed pads and PCB copper areas for heat dissipation. It is recommended that worst case junction temperature be measured for both High-Side MOSFET and Low-Side MOSFET to ensure that they are operating within Safe Operating Area (SOA).

#### **PWM Input**

AOZ5007AQI is compatible with 5V (CMOS) PWM logic. Refer to Figure 1 for PWM logic timing and propagation delays diagram between PWM input and the MOSFET gate drives. AOZ5007AQI is compatible with 5V (CMOS) PWM logic. Refer to Figure 1 for PWM logic timing and propagation delays diagram between PWM input and the MOSFET gate drives.

The PWM is also compatible with Tri-State input. When the PWM output from the external PWM controller is in high impedance or not connected both High-Side and Low-Side MOSFETs are turned off and VSWH is in high impedance state. Table 1 shows the thresholds level for high-to-low and low-to-high transitions as well as Tri-State window.

There is a Holdoff Delay between the corresponding PWM Tri-State signal and the MOSFET gate drivers to prevent spurious triggering of Tri-State mode which may be caused by noise or PWM signal glitches. The Holdoff Delay is typically 175ns.

Table 1. PWM Input and Tri-State Thresholds

Thresholds $\rightarrow$	$V_{PWMH}$	$V_{PWML}$	$V_{TRIH}$	$V_{TRIL}$
AOZ5007AQI	4.2V	0.72V	1.6V	3.4V

Note: See Figure 2 for propagation delays and Tri-State window.



#### **Diode Mode Emulation of Low-Side MOSFET (FCCM)**

AOZ5007AQI can be operated in the diode emulation or pulse skipping mode using FCCM (Pin 1). This enables the converter to operate in asynchronous mode during start up, light load or under pre-bias conditions.

When FCCM is high, the module will operate in Continuous Conduction Mode (CCM). The Driver logic will use the PWM signal and generate both the High-Side and Low-Side complementary gate drive outputs with minimal anti-overlap delays to avoid cross conduction.

When FCCM is low, the module can operate in Discontinuous Conduction Mode (DCM). The High-Side MOSFET gate drive output is not affected but Low-Side MOSFET will enter diode emulation mode. See Table 2 for the truth table for PWM and FCCM inputs.

**Table 2. Control Logic Truth Table** 

FCCM	FCCM PWM		GL
L	L	L	H if $I_L > 0A$ L if $I_L < 0A$
L	Н	Н	L
Н	H L		Н
Н	Н	Н	L
L	L Tri-State H Tri-State		L
Н			L
Tri-State	Х	L	L

Note: Diode Emulation mode is activated when FCCM pin is LOW.

#### **Gate Drives**

AOZ5007AQI has an internal high current high speed driver that generates the floating gate driver for the High-Side MOSFET and a complementary driver for the Low-Side MOSFET. An internal shoot-through protection scheme is implemented to ensure that both MOSFETs cannot be turned on at the same time. The operation of PWM signal transition is illustrated as below.

1) PWM from logic Low to logic High

When the falling edge of Low-Side Gate Driver output GL goes below 1V, the blanking period is activated. After a pre-determined value (t<sub>PDHU</sub>), the complementary High-Side Gate Driver output GH is turned on.

2) PWM from logic High to logic Low

When the falling edge of switching node VSWH goes below 1V, the blanking period is activated. After a predetermined value (t<sub>PDHL</sub>), the complementary Low-Side Gate Driver output GL is turned on.

This mechanism prevents cross conduction across the input bus line VIN and PGND. The anti-overlap circuit monitors the switching node VSWH to ensure a smooth transition between the two MOSFETs under any load transient conditions.



#### **PCB Layout Guidelines**

AOZ5007AQI is a high current module rated for operation up to 2MHz. This requires high switching speed to keep the switching losses and device temperatures within limits. An integrated gate driver within the package eliminates driver-to-MOSFET gate pad parasitic of the package or on PCB.

To achieve high switching speeds, high levels of slew rate (dv/dt and di/dt) will be present throughout the power train which requires careful attention to PCB layout to minimize voltage spikes and other transients. As with any synchronous buck converter layout, the critical requirement is to minimize the path of the primary switching current loop formed by the High-Side MOSFET, Low-Side MOSFET, and the input bypass capacitor C<sub>IN</sub>. The PCB design is greatly simplified by the optimization of the AOZ5007AQI pin out. The power inputs of VIN and PGND are located adjacent to each other and the input bypass capacitors C<sub>IN</sub> should be placed as close as possible to these pins. The area of the secondary switching loop is formed by Low-Side MOSFET, output inductor L1, and output capacitor C<sub>OUT</sub> is the next critical requirement. This requires second layer or "Inner 1" to be the PGND plane. VIAs should then be placed near PGND pads.

While AOZ5007AQI is a highly efficient module, it still dissipates a significant amount of heat under high power conditions. Special attention is required for thermal design. MOSFETs in the package are directly attached to individual exposed pads (VIN and PGND) to simplify thermal management. Both VIN and VSWH pads should be attached to large areas of PCB copper. Thermal relief pads should be placed to ensure proper heat dissipation to the board. An inner power plane layer dedicated to VIN, typically the high voltage system input, is desirable and VIAs should be provided near the device to connect the VIN pads to the power plane. Significant amount of heat can also be dissipated through multiple PGND pins. A large copper area connected to the PGND pins in addition to the system ground plane through VIAs will further improve thermal dissipation.

As shown on Figure. 11, the top most layer of the PCB should comprise of wide and exposed copper area for the primary AC current loop which runs along VIN pad originating from the input capacitors C10, C11, and C12 that are mounted to a large PGND pad. They serve as thermal relief as heat flows down to the VIN exposed pad that fans out to a wider area. Adding VIAs will only help transfer heat to cooler regions of the PCB board through the other layers beneath but serve no purpose to AC activity as all the AC current sees the lowest impedance on the top layer only.

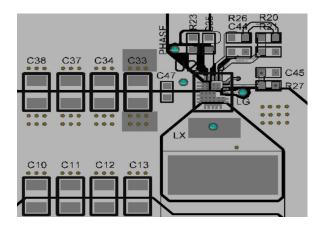


Figure 11. Top Layer of Demo Board, VIN, VSWH and PGND Copper Pads

As the primary and secondary (complimentary) AC current loops move through VIN to VSWH and through PGND to VSWH, large positive and negative voltage spikes appear at the VSWH terminal which are caused by the large internal di/dt produced by the package parasitic. To minimize the effects of this interference at the VSWH terminal, at which the main inductor L1 is mounted, size just enough for the inductor to physically fit. The goal is to employ the least amount of copper area for this VSWH terminal, only enough so the inductor can be securely mounted.

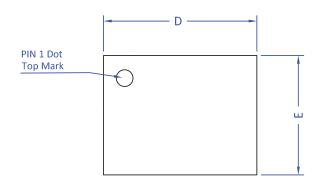
To minimize the effects of switching noise coupling to the rest of the sensitive areas of the PCB, the area directly underneath the designated VSWH pad or inductor terminal is voided and the shape of this void is replicated descending down through the rest of the layers.

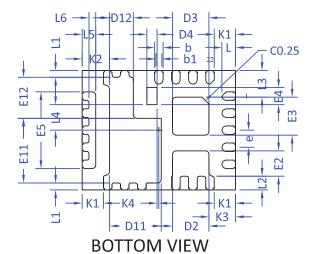
Positioning VIAs through the landing pattern of the VIN and PGND thermal pads will help quickly facilitate the thermal build up and spread the heat much more quickly towards the surrounding copper layers descending from the top layer. (See RECOMMENDED LANDING PATTERN AND VIA PLACEMENT section).

The exposed pads dimensional footprint of the 3.5x4.5 QFN package is shown on the package dimensions page. For optimal thermal relief, it is recommended to fill the PGND and VIN exposed landing pattern with 10mil diameter VIAs. 10mil diameter is a commonly used via diameter as it is optimally cost effective based on the tooling bit used in manufacturing. Each via is associated with a 20mil diameter keep out. Maintain a 5mil clearance (127um) around the inside edge of each exposed pad in an event of solder overflow, potentially shorting with the adjacent expose thermal pad.

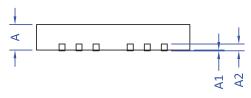


## Package Dimensions, QFN3.5x4.5-22L



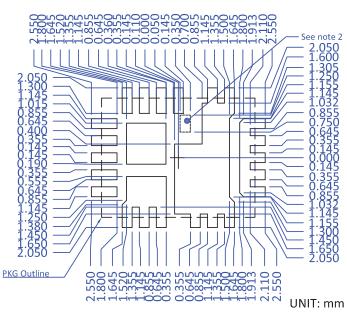


# **TOP VIEW**



SIDE VIEW

## RECOMMENDED LAND PATTERN



CVMADOLC	DIMENSION IN MM			DIMENSION IN INCHES			
SYMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.70	0.75	0.80	0.028	0.030	0.031	
A1	0.00	-	0.05	0.000	-	0.002	
A2		0.20REF			0.008REF		
Е	3.40	3.50	3.60	0.134	0.138	0.142	
E11	1.85	1.90	1.95	0.073	0.075	0.077	
E12	1.15	1.20	1.25	0.045	0.047	0.049	
E2	0.70	0.75	0.80	0.027	0.029	0.031	
E3	1.07	1.12	1.17	0.042	0.044	0.046	
E4	0.45	0.50	0.55	0.018	0.020	0.022	
E5	2.20	2.25	2.30	0.087	0.089	0.091	
D	4.40	4.50	4.60	0.173	0.177	0.181	
D11	1.47	1.52	1.57	0.058	0.060	0.062	
D12	0.65	0.70	0.75	0.026	0.028	0.030	
D2	1.02	1.07	1.12	0.040	0.042	0.044	
D3	1.02	1.07	1.12	0.040	0.042	0.044	
D4	0.25	0.30	0.35	0.010	0.012	0.014	
L	0.35	0.40	0.45	0.014	0.016	0.018	
L1	0.15	0.20	0.25	0.006	0.008	0.010	
L2	0.35	0.40	0.45	0.014	0.016	0.018	
L3	0.73	0.78	0.83	0.029	0.031	0.033	
L4	0.70	0.75	0.80	0.028	0.030	0.031	
L5	0.35	0.40	0.45	0.014	0.016	0.018	
L6	0.15	0.20	0.25	0.006	0.008	0.010	
K1	0.58	0.63	0.68	0.023	0.025	0.027	
K2	0.75	0.80	0.85	0.030	0.031	0.033	
К3	0.73	0.78	0.83	0.029	0.031	0.033	
K4	0.00	0.05	0.10	0.000	0.002	0.004	
b	0.20	0.25	0.30	0.008	0.010	0.012	
b1	0.13	0.18	0.23	0.005	0.007	0.009	
е	e 0.50BSC				0.02BSC		

#### NOTE:

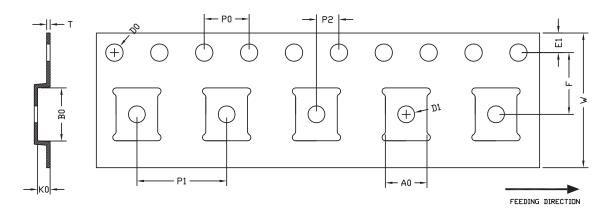
1. CONTROLLING DIMENSION IS MILLIMETER.

CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

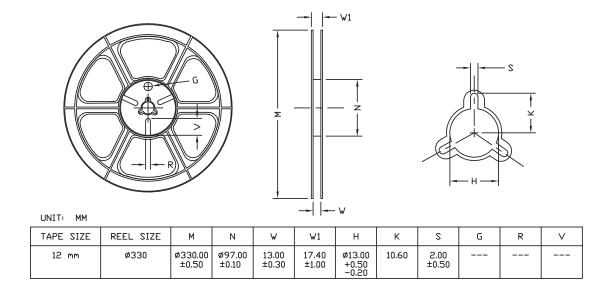
2. DOTTED OUTLINE IS GUIDELINE TO BE COMPATIBLE WITH INDUSTRY COMMON LAYOUT BUT NOT RECOMMENDED BY AOS.



# Tape and Reel Drawing, QFN3.5x4.5-22L

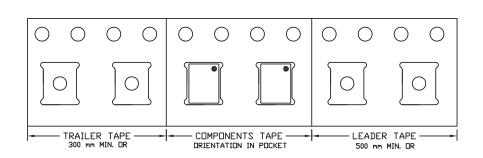


UNIT: MM PACKAGE D0 D1 W E1 F P0 P1 P2 Т Α0 B0 K0 3.71 4.71 1.55 1.50 12.00 1.75 5.50 4.00 8.00 2.00 0.30 1.11 QFN4.5×3.5 ±0.10 ±0.10 ±0.10 ±0.05 ±0.30 ±0.10 ±0.10 ±0.10 ±0.10 ±0.10 ±0.05



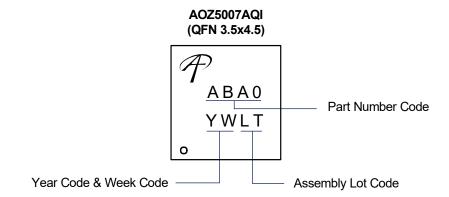
Leader / Trailer & Orientation

Unit Per Reel: 5000pcs





#### **Part Marking**



#### **LEGAL DISCLAIMER**

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#### As used herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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